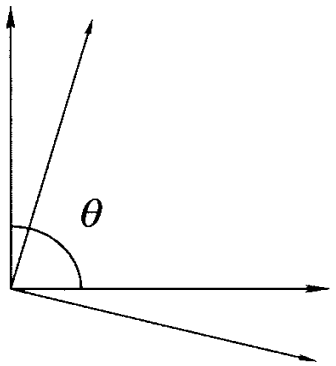

FIG. 1(a)

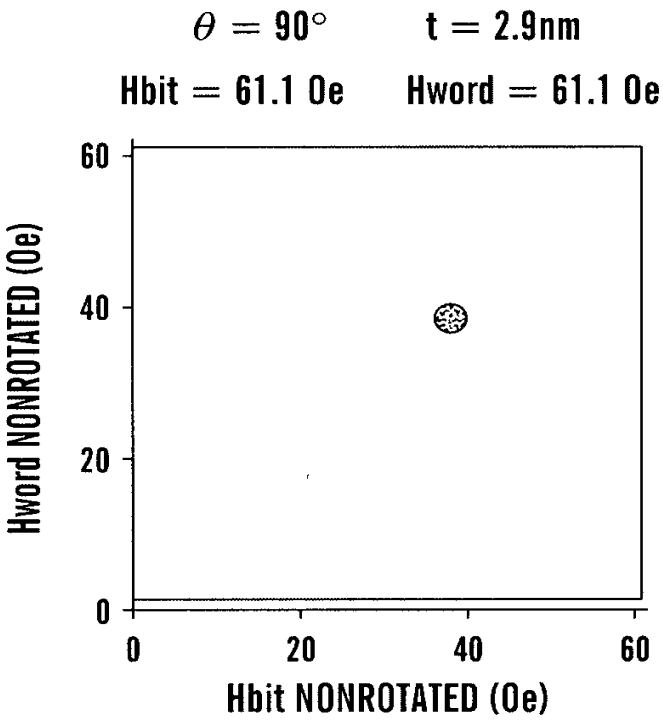

FIG. 1(b)

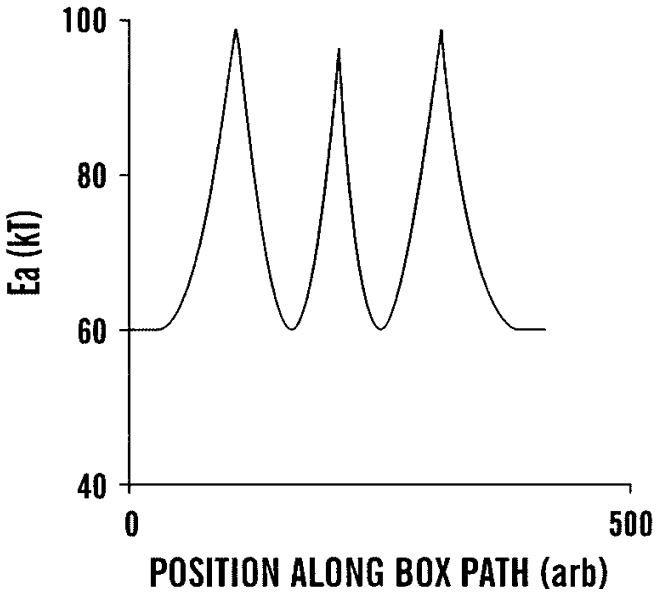

FIG. 1(c)

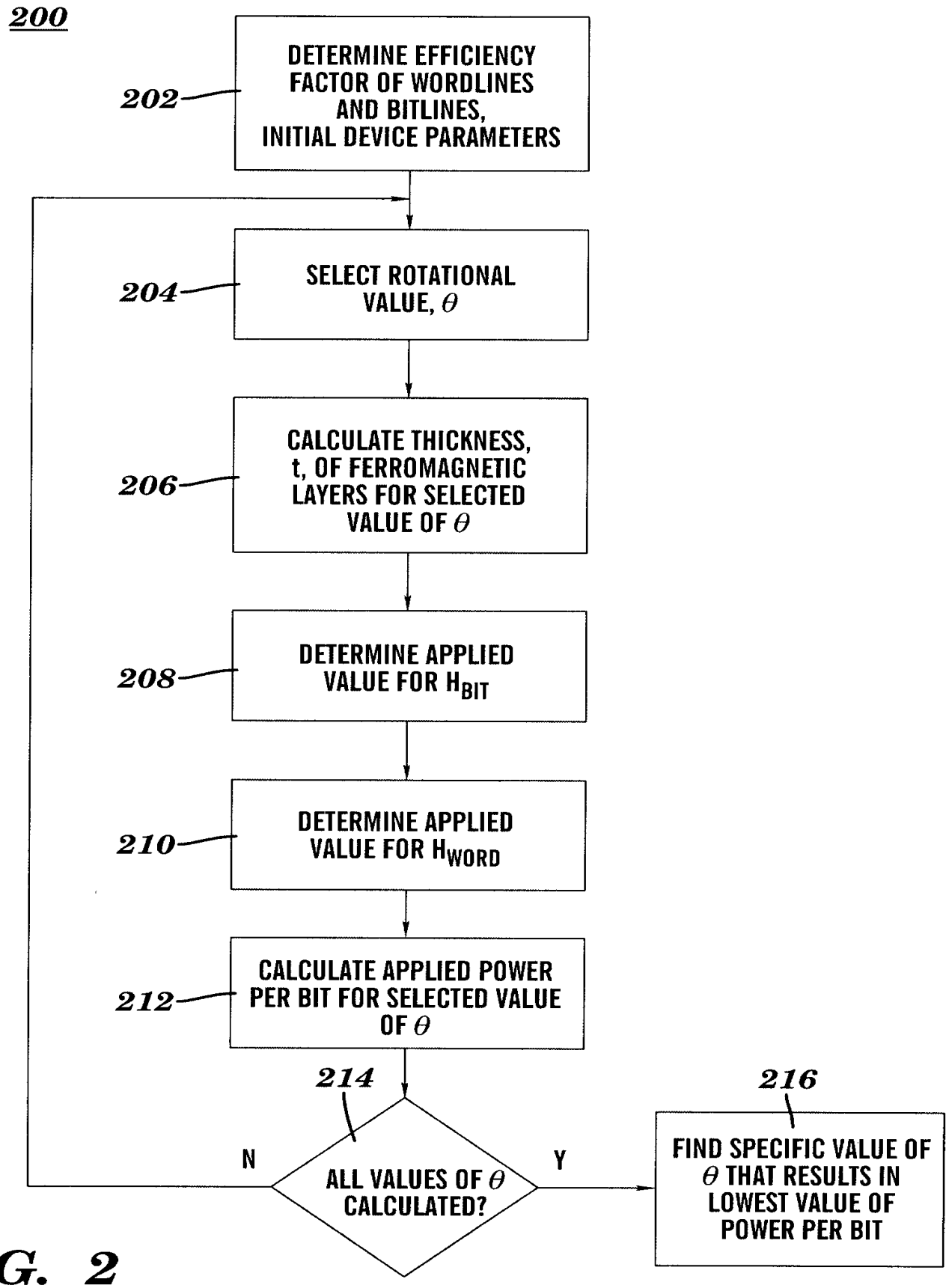
200
202
DETERMINE EFFICIENCY FACTOR OF WORDLINES AND BITLINES, INITIAL DEVICE PARAMETERS
204
SELECT ROTATIONAL VALUE, θ
206
CALCULATE THICKNESS, t, OF FERROMAGNETIC LAYERS FOR SELECTED VALUE OF θ
208
DETERMINE APPLIED VALUE FOR H_{BIT}
210
DETERMINE APPLIED VALUE FOR H_{WORD}
212
CALCULATE APPLIED POWER PER BIT FOR SELECTED VALUE OF θ
214
ALL VALUES OF θ CALCULATED?
N
Y
216
FIND SPECIFIC VALUE OF θ THAT RESULTS IN LOWEST VALUE OF POWER PER BIT

FIG. 2

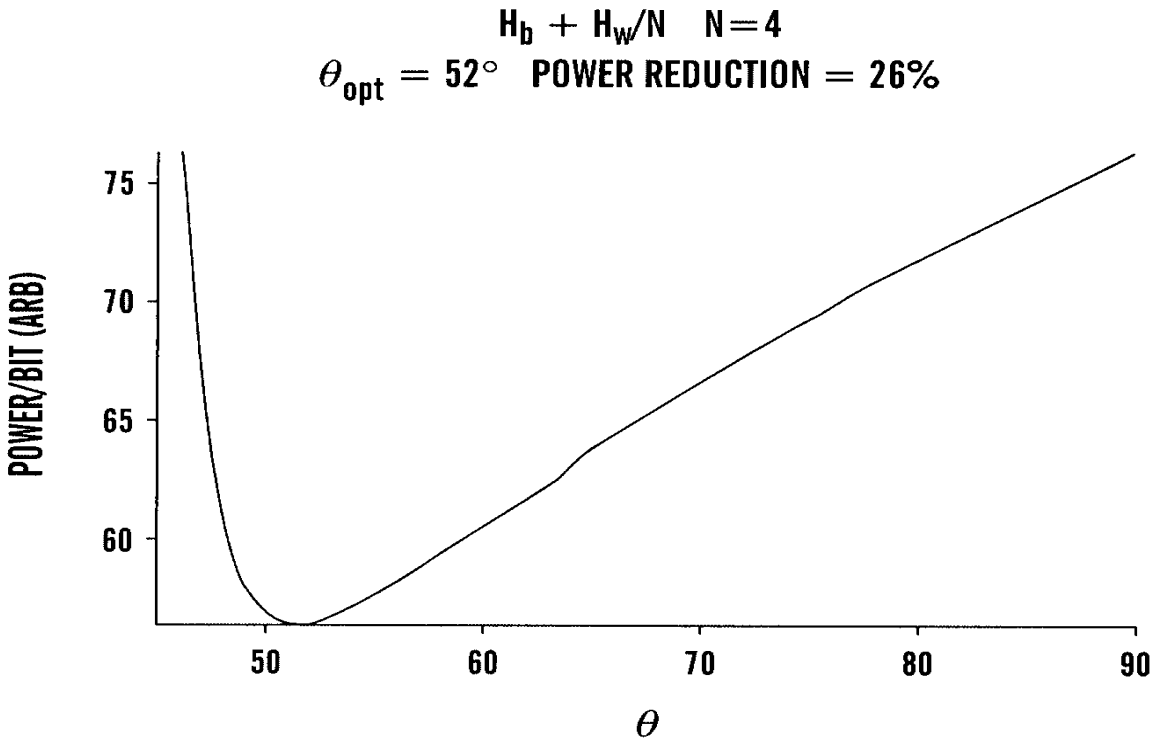

FIG. 3(a)

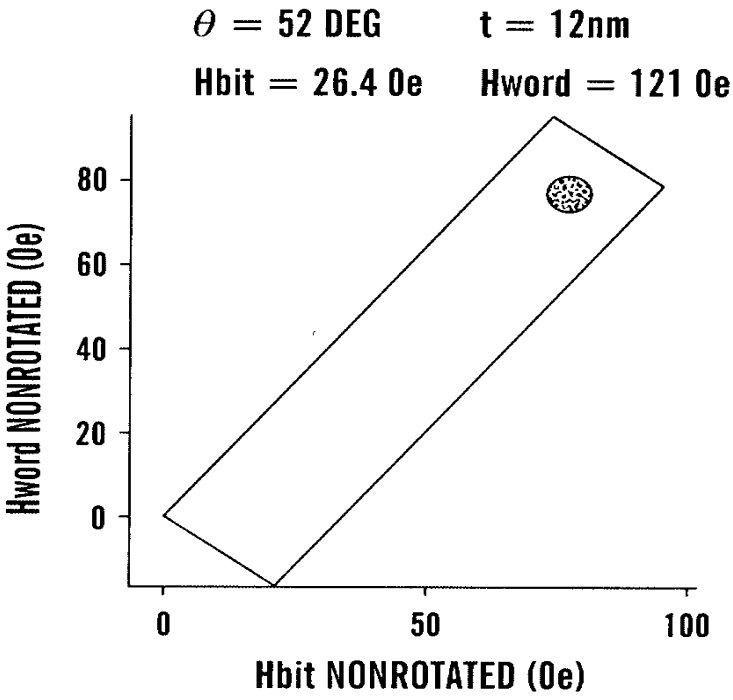

FIG. 3(b)

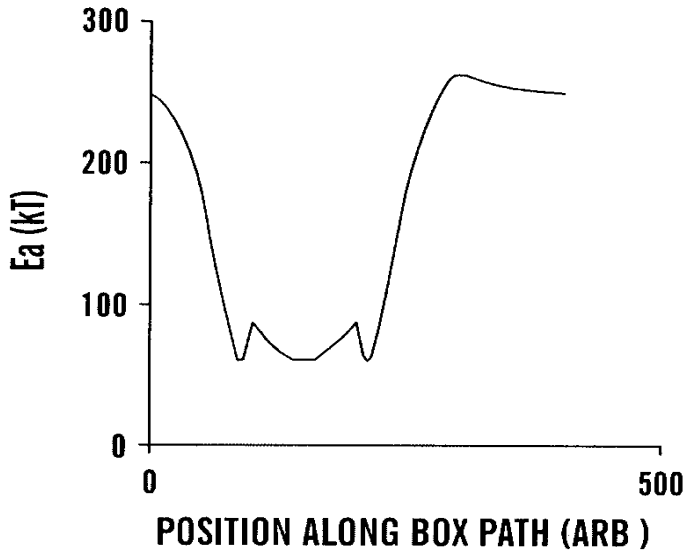

FIG. 3(c)

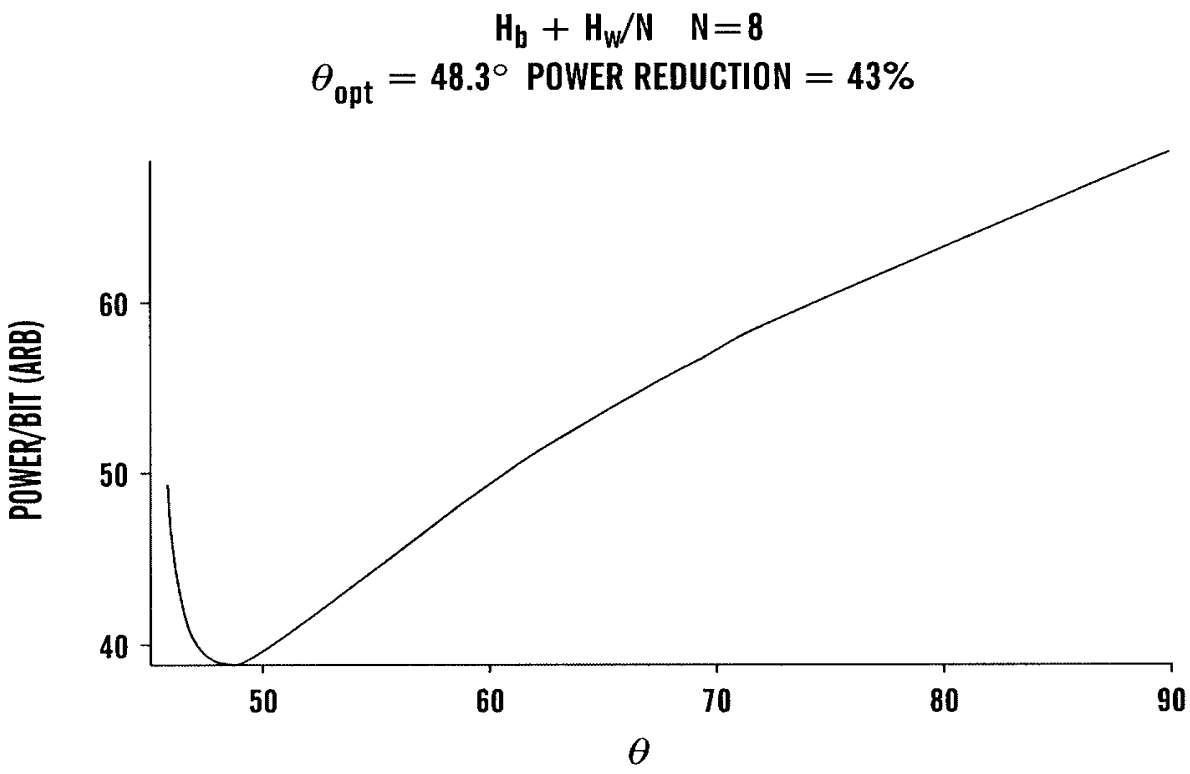

FIG. 4(a)

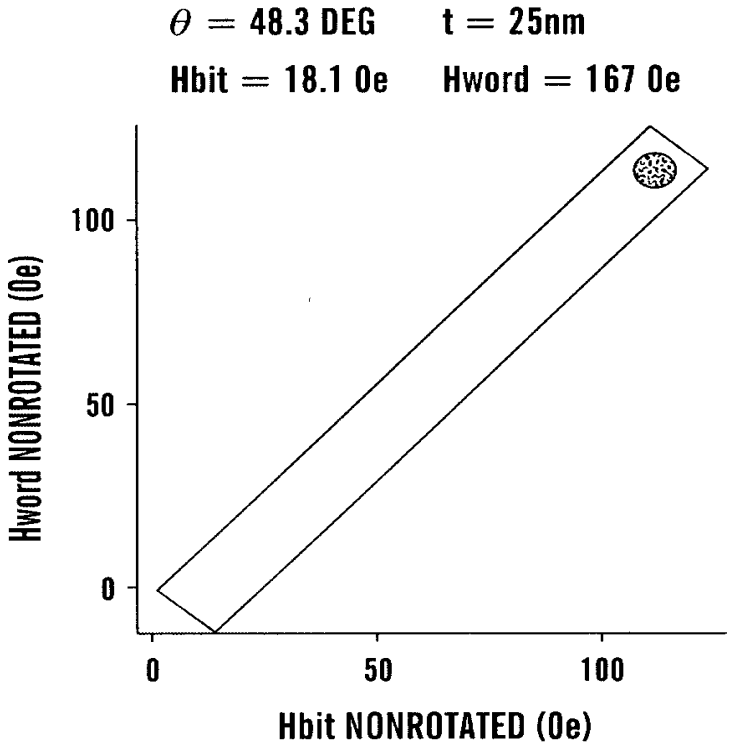

FIG. 4(b)

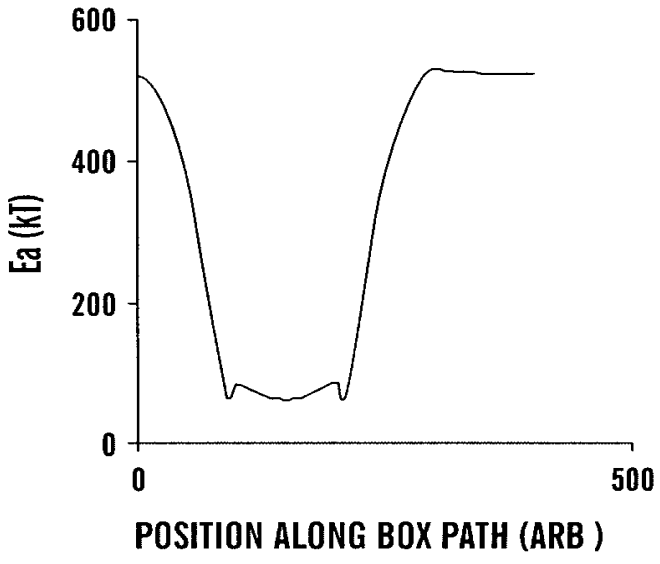

FIG. 4(c)

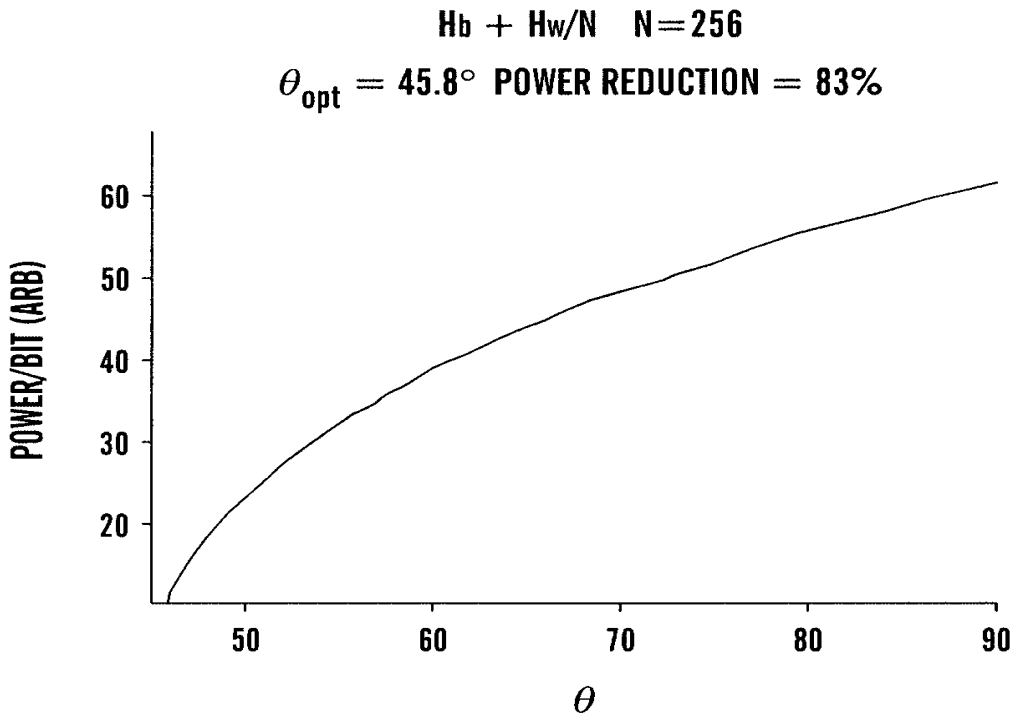

FIG. 5(a)

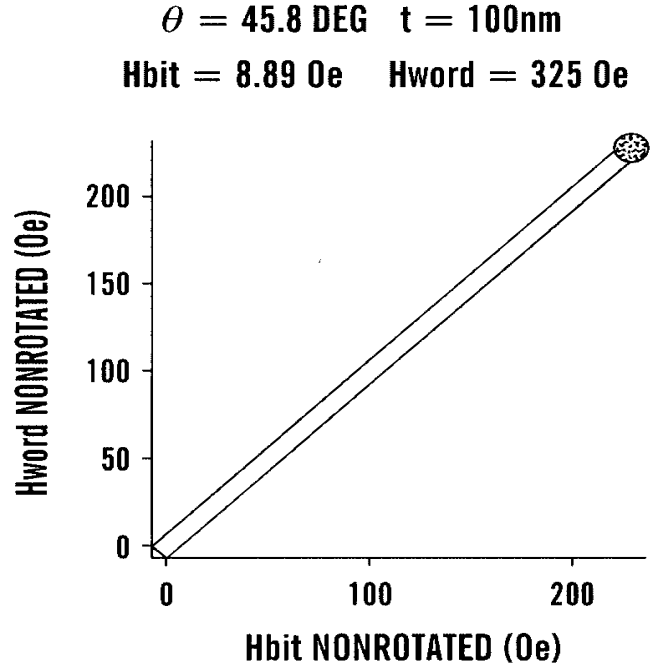

FIG. 5(b)

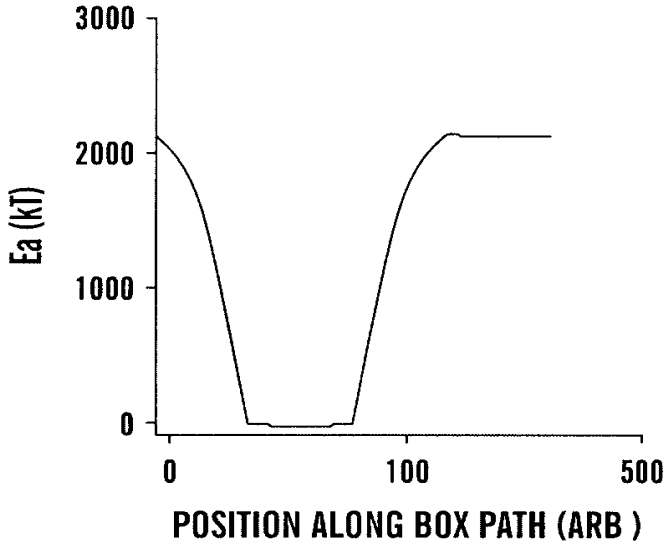

FIG. 5(c)

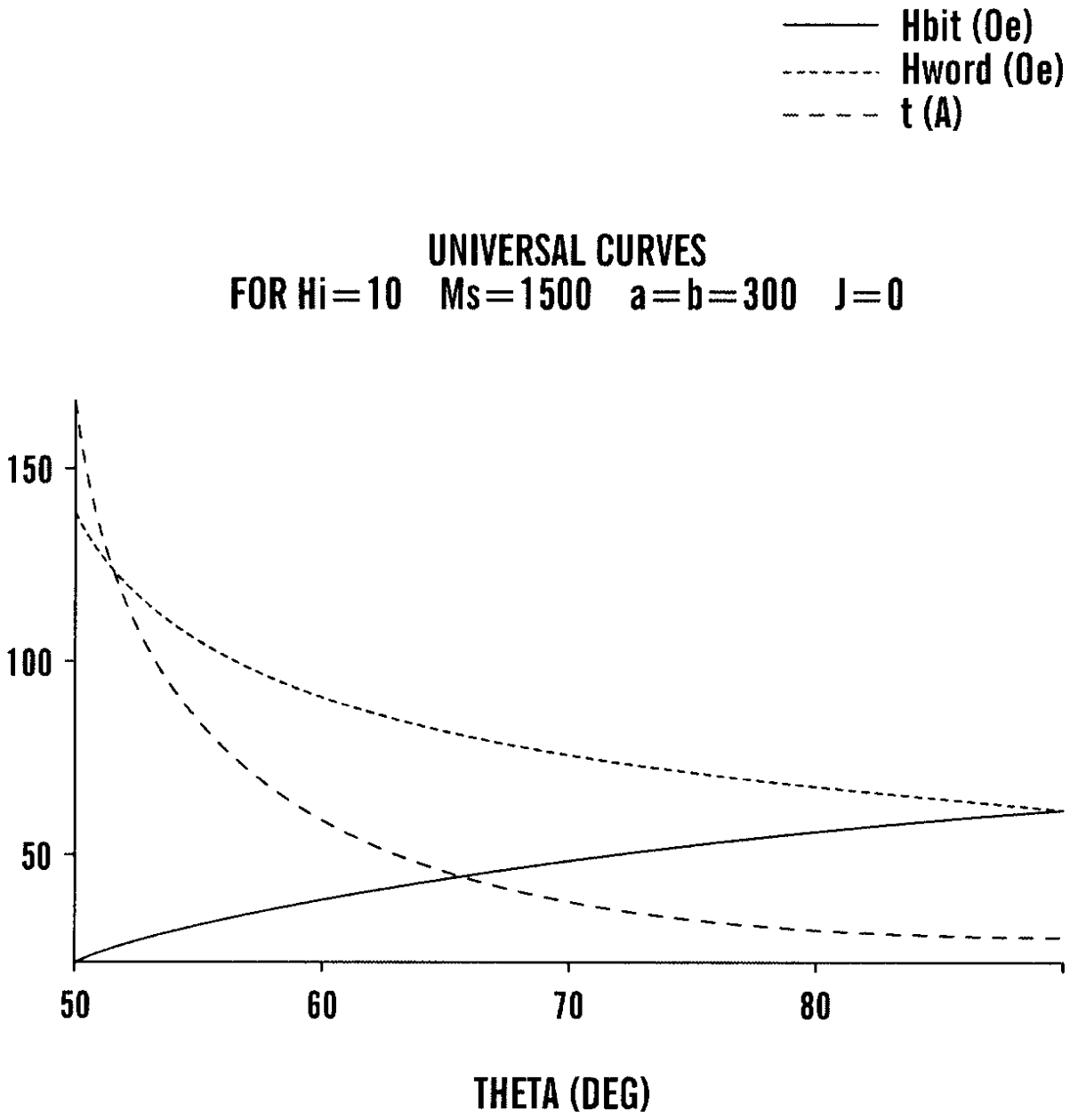
Hbit (Oe)
Hword (Oe)
t (A)
UNIVERSAL CURVES
FOR Hi=10 Ms=1500 a=b=300 J=0
150
100
50
50
60
70
80
THETA (DEG)

FIG. 6(a)

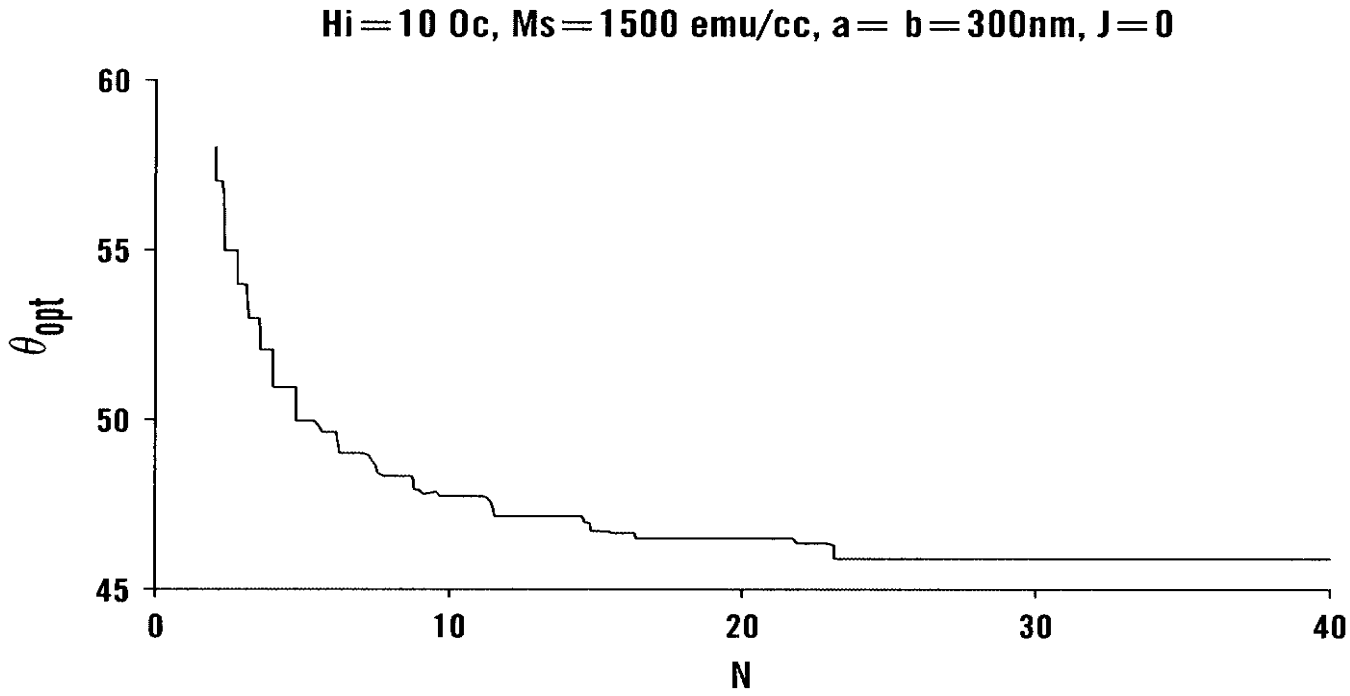
Hi=10 Oc, Ms=1500 emu/cc, a= b=300nm, J=0
60
55
50
45
θ_{opt}
0
10
20
30
40
N

FIG. 6(b)

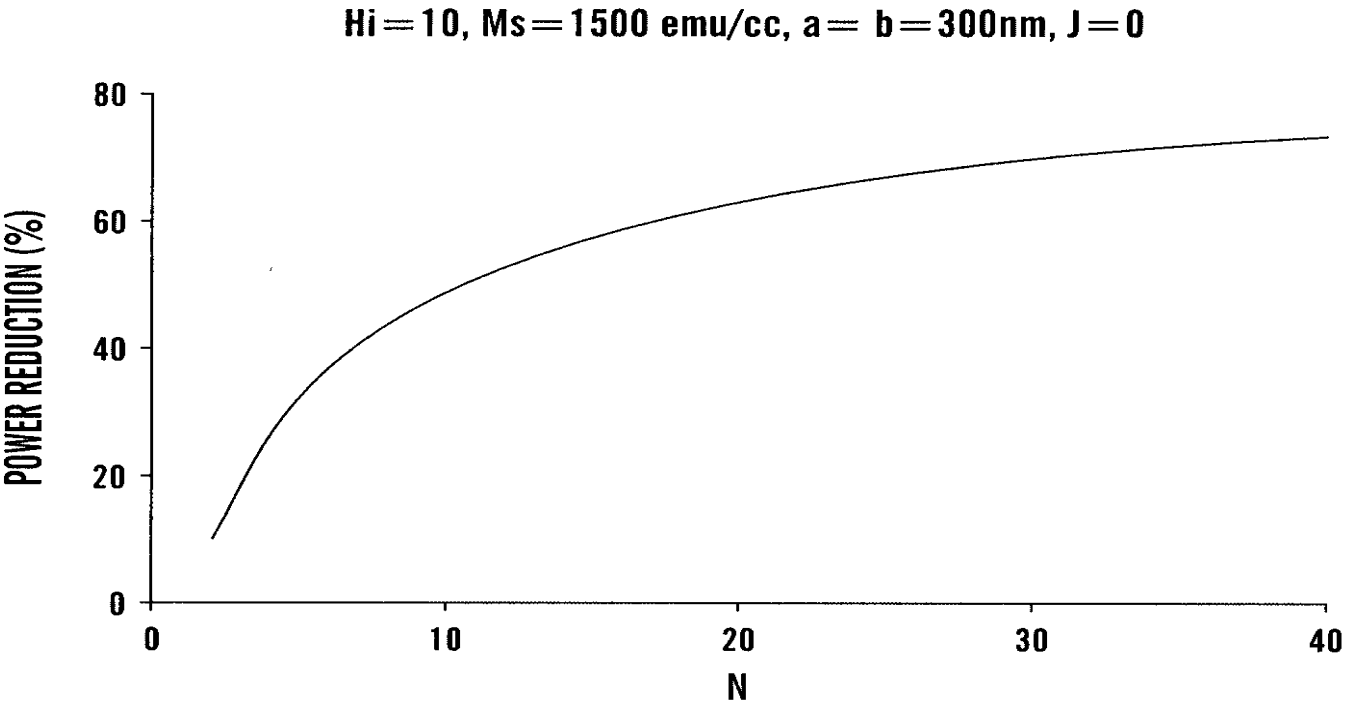
Hi=10, Ms=1500 emu/cc, a= b=300nm, J=0
80
60
40
20
0
POWER REDUCTION (%)
0
10
20
30
40
N

FIG. 6(c)

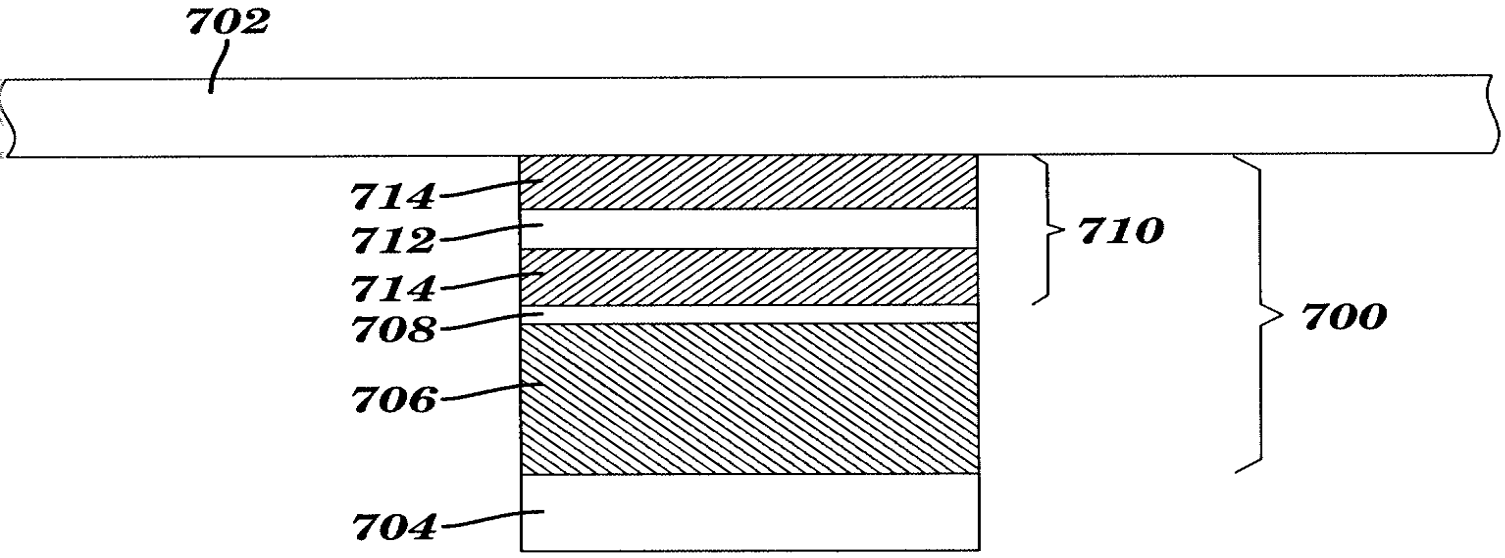

FIG. 7

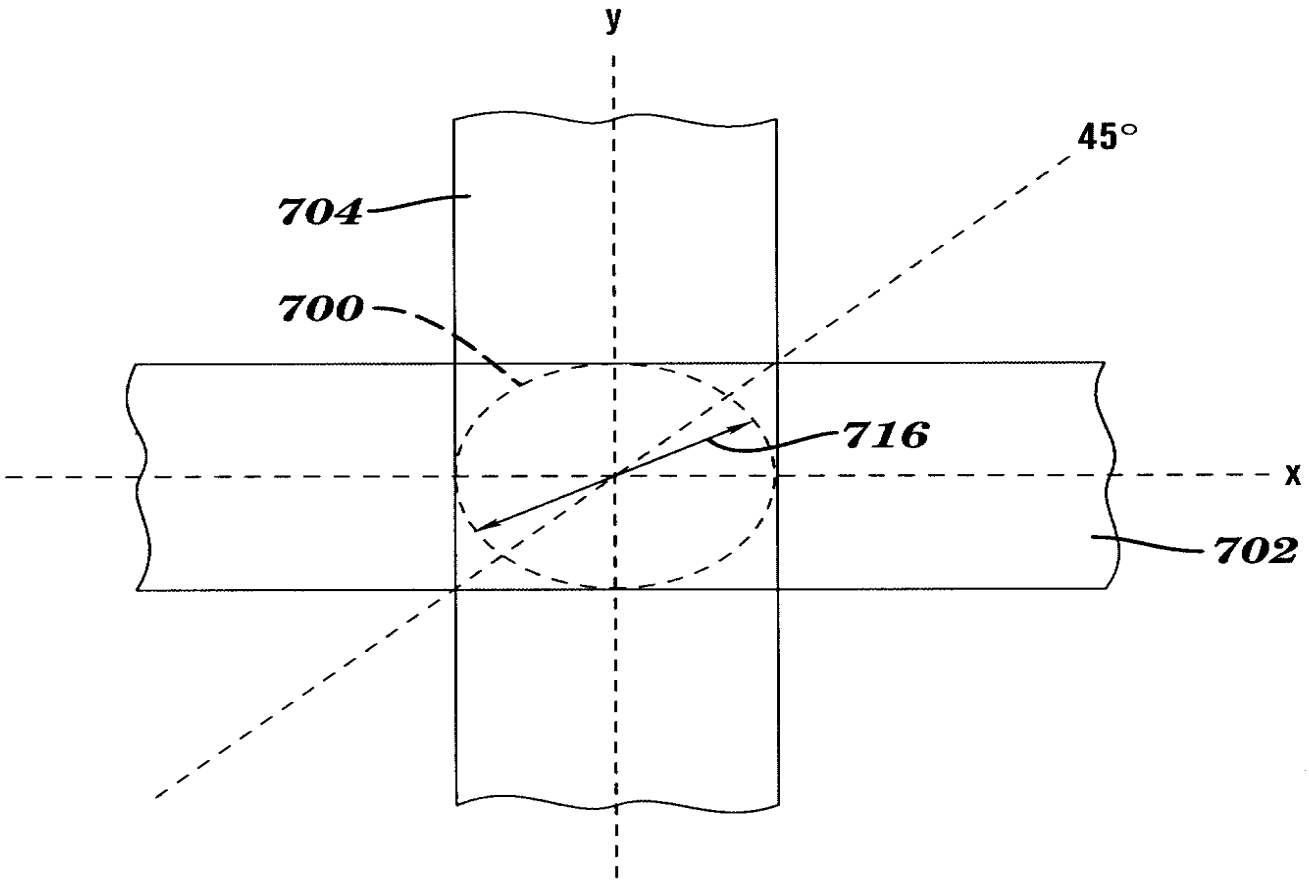

FIG. 8